ASPECTS OF ZNO AND ITSELECTRICAL AND OPTICAL PROPERTIES

KRISHNA GOPAL PRADHAN (M.Sc), Research Scholar, Deptt. of Physics, CMJ University, Jorabat.
DR PRINCE BANSAL, Research Supervisor, Deptt. of Physics, CMJ University, Jorabat.

ABSTRACT

ZnO and its qualities are the focus of this article. Zinc Oxide (ZnO) has been studied for its usual qualities, which are discussed in this article. Doping ZnO with either cation substitution from Group III elements or anion substitution from Group VII elements is simple and straightforward. Al, Ga, and In are the most often utilised dopants, resulting in high-quality films with excellent conductivity. While n-type ZnO can be easily made, the question of how to make p-type ZnO is still up for dispute. When anions from Group I on Oxygen sites doped with cations from Group I are used, ZnO is considered p-type. Group V dopants, such as N, As, P, and Sb, were of particular interest to researchers. ZnO may be used in electrical and opto-electronic devices because of its direct and broad band gap. Zinc oxide has long been regarded as one of the semiconductor industry's most radiation resistant materials. Its radiation resistance has been the subject of several studies.

Keywords: ZNO, Properties, Thin, Electrical, Optical, Ferroelectricity

1. INTRODUCTION

All semiconducting materials have had a significant impact on engineering, but silicon has been the most influential. Gallium Arsenide is the most important compound semiconductor of type III-V and II-VI. Researchers have recently been interested in Gallium Nitride and Zinc Oxide due to their wide range of applications. At normal temperature, both materials display similar characteristics and excellent transparency. As a possible replacement for gallium nitride in laser diodes that generate ultraviolet and blue light, Zinc Oxide has drawn considerable attention. In comparison to Gallium Nitride, it has a higher exciton binding energy at ambient temperature (>60 meV) and lower power thresholds for optical pumping, as well as a band gap energy that can be modified from 2.8 to 4.0 eV by doping it with various materials.

Zinc oxide has long been regarded as one of the semiconductor industry's most radiation resistant materials. The radiation-resistant qualities of this material were studied in a number of experiments. The ZnO films were examined by Karuppasamy for their structural, optical, and luminescent characteristics. In the photoluminescence spectra, a free exciton peak was found following electron irradiation. The electron bombardment on the film's surface was blamed for all of these alterations in the material characteristics. Because of this, it was determined that the heating impact of electron bombardment was unique from that of traditional thermal annealing The production of oxygen and Zn vacancies in electron-irradiated ZnO crystals was examined by Kappers using optical and Electron Paramagnetic Resonance techniques. Kuriyama investigated the photoconductivity and thermally stimulated current in single crystal bulk ZnO caused by electron irradiation defects and discovered an Oxygen vacancy defect.

2. ZNO-ITSPROPERTIES

It has been discussed in this section how Zinc Oxide (ZnO) is used. There are two main crystal structures used by II-VI Group compounds: cubic Zinc-Blend and Wurtzite. At the four corners of the tetrahedron, the four cations surround the four anion centres, and vice versa. Sp3 covalent bonding is used to hold these materials together, but they also have significant ionic properties. There are two overlapping hexagonal-close-pack sublattices in the Wurtzite type ZnO structure, each of which is formed of one atom type, and they are distanced from each other along the C-axis by u=3/8=0.375.

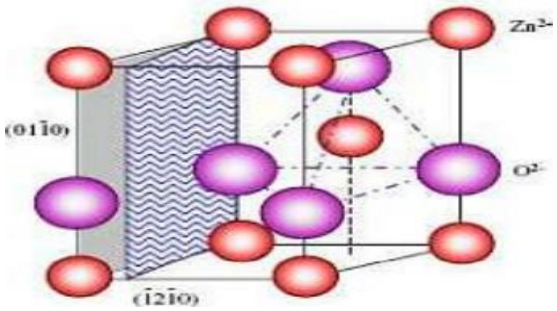

Fig.1 Wurtzite structureofZnO.

There are four atoms per unit cell in each sub-lattice and each atom of one kind of Group II is surrounded by four of another kind of Group VI or the other way around. C/A ratio and the u value of actual ZnO crystals diverge from Wurtzite's ideal configuration. Notice how the c/a ratio and u parameter have a strong relationship. Because long-range polar interactions distort tetrahedral angles, these four tetrahedral distances stay almost constant during a distortion of tetrahedral angle. If the following relation is true, then these two slightly differing bond lengths will be equivalent:

$$u = \left(\frac{1}{3}\right)\left(\frac{a^2}{c^2}\right) + \frac{1}{4}$$

In terms of the ideal c/a ratio, components with greater variances in electro negativity are more likely to deviate from the ideal c/a ratio. Table 1 lists the most important physical properties of ZnO. Since its unique ability to bind diverse dopants into the lattice has been studied extensively for several years, it has been used in a variety of applications. These dopants for ZnO will be described in further detail later on in this section.

In the 1920s, ZnO detectors for radio sets were the first practical use of the material. Low power threshold for optical pumping and radiation hardness of ZnO make it possible to realise applications by harnessing its inherent features such as ZnO's diverse chemical properties. This material, according to research, is more radiation resistant than Gallium Nitride, making it an excellent choice for use in space and nuclear power plants, respectively.

Table1Various parameters ofZnO

Appearance	AmorphousWhite/YellowishWhitepowder
Density	5.606g/cc
M.P.	1975 C
B.P.	2360 C
SolubilityinWater	0.16 mg/100 mL
c-parameter	5.21A
a/c	1.633A
*u*parameter	0.345
Stablephase (300K)	Wurtzite
Staticdielectricconstant	8.656
RefractiveIndex	2.01
OpticalBandgap	3.3eV
ExcitonBindingenergy	60 meV
Intrinsiccarrierconcentration	$<10^6$/cc
Electronmobility(300K)	200cm^2/VSec
Holemobility(300 K)	5-50cm^2/VSec
Holeeffectivemass	0.59

ZnO-based thin films have recently acquired interest for usage in applications such as thin-film transistors, thin-film solar cells, electrical circuits, and flat panel displays, among others. Because of its increased electron mobility as a high band gap semiconductor, ZnO is well-

suited for high power and high temperature electrical devices. Since ZnO thin films have a high piezoelectric constant, they have been employed as surface acoustic wave devices.
The n-type conductivity of ZnO and its intrinsic flaws is evident even when the material is not doped. Vacancies, interstitials, and anti-sites, all types of native defects, may play an important role that has yet to be fully discovered. Native deficiencies have been shown to cause shallow donor states. Look et al. believe that a Zni-based n-type conductivity in ZnO operates like a shallow donor, rather than Vo. However, some new experimental and theoretical investigations indicate that Zni are unstable and diffuse at RT, whereas Vo are deep compensating defects and are not responsible for the n-type conductivity, acting like shallow donors, in ZnO. This contradicts previous experimental and theoretical findings. ZnO conductivity is mostly due to hydrogen and Group III element impurities, according to these investigations. Van de Walle's theoretical work suggested that interstitial H in ZnO acts as a shallow donor, and this was later validated experimentally. In addition, the conductivity of thin films produced in H2 using the Pulsed Laser Deposition process increased by three orders of magnitude in our experimental investigations. Ca-H complexes, in which Ca gives an electric charge to an adjacent O atom to trap H, were shown by Secondary Ion Mass Spectroscopy to allow it to operate as a shallow donor. Substitutive H, unlike interstitial H, is stable and has high migration energy making it a great choice for donating electrons in as-grown ZnO. In order to effectively dope ZnO and completely utilise its inherent capabilities, it is necessary to first properly understand and regulate the impacts of each of these innate flaws.

2.1 n-typedoping

Doping ZnO with either cation substitution from Group III elements or anion substitution from Group VII elements is simple and straightforward. In addition to Al, Ga and In, the most often used dopants, these films were of good quality. Myong and Ataev observed resistivity values of 6.2x10-4 and 1.2x10-4-cm, respectively, for ZnO doped with Al and Ga. To make n-type layers for electronic devices, thin films with carrier concentrations as high as 1021 cm-3 have been developed.

2.2 p-typedoping

While n-type ZnO can be easily made, the question of how to make p-type ZnO is still up for dispute. When anions from Group I on Oxygen sites doped with cations from Group I are used, ZnO is considered p-type. Group V dopants, such as N, As, P, and Sb, were of particular interest to researchers. Group I elements, according to theoretical investigations, are shallow acceptors. Group V elements, on the other hand, are strong acceptors. Doping in Group I produce less disruption and shallower flaws than doping in Group V. The tiny size of Group I components, on the other hand, allows them to more easily occupy interstitial positions. Anti-sites can be more easily formed in P due to its much longer bond length. Because of its similar bond length to Zn, low ionisation energy, and low probability of anti-site formation, N is theoretically preferred among Group V elements.

3. ELECTRICALPROPERTIES

ZnO may be used in electrical and opto-electronic devices because of its direct and broad band gap. Thin ZnO films were studied electrically by Zabinski. Electrons are transferred to the conduction band from donor levels formed by interstitial Zn atoms, which explains the conduction process. ZnO conduction may also be caused by a lack of oxygen. Oxygen vacancies are a majority defect in ZnO, hence Zn interstitial defects are also donors. In terms of transport qualities, it is the grain boundaries that matter most. Atoms are concentrated around the grain boundary or just a few layers away from it. The electrical characteristics of materials can be studied using these. Properties such as degree of structural regularity, variation in electrical conduction routes, stabilities, deterioration, and time-dependent processes can all be examined.

4. OPTICALPROPERTIES

Optical absorption, transmission, reflection, photo refraction, spectroscopic ellipsometry, photoluminescence, cathode luminescence, calorimetric spectroscopy have all been used to study ZnO's optical characteristics. Excitonic characteristics, donor- and acceptor-bound excitons, LO-phonon duplicates of the primary excitonic emissions, and the donor-acceptor pair transition are all crucial to understanding how these processes work.

4.1 Freeexcitons

When it comes to the valence band of ZnO, the crystal and spin-orbit interactions affect the crystal and spin-orbit interactions to create the Wurtzite structure. The transition from these valence bands will dominate the near-band gap intrinsic emission. Transitions between the conduction and valence bands, or vice versa, are made by the heavy and light holes. Consequently, these three valence bands dominate the near-band-gap intrinsic absorption and emission spectra. For his thesis, Thomas looked at ZnO's basic absorption edge and split crystal band. Chichibu identified distinct excitonic resonances in the light reflectance spectra of ZnO epitaxial layers produced on ScAlMgO4 substrates via laser MBE.

4.2 Boundexcitons

Excitons bound to dopants or defects in the band gap are the transitions that impact both optical absorption and emission processes by creating discrete electronic states in the band gap. The confined excitons' electronic states are highly dependent on the band structure and semiconductor material of the system. Excitons might theoretically be bound to both neutral and charged donors and acceptors in a chemical reaction. When describing the bound excitons for neutral donors and acceptors, the dominating coupling between comparable particles at the bound exciton states is a simple way to put it. Because of the existence of donors owing to accidental or doped impurities and/or shallow donor-like defects in ZnO, the neutral shallow donor bound exciton often prevails.

5. CONCLUSION:

When exposed to electron and Gamma radiations, Lithium doped zinc oxide thin films exhibit structural, ferroelectric, dielectric, electrical, as well as optical characteristics. The primary goal of this study was to determine the films' radiation resistance to two different types of irradiation. ZnO's radiation resistance has been well documented in the scientific literature. This study, however, demonstrates that ZnO alters its characteristics when exposed to radiation. If they are to be used in radiation-resistant memory devices, the deterioration in their ferroelectric characteristics must be handled effectively. Either electrons or Gamma radiations interact with matter differently than fast heavy ion irradiation. In certain cases, the radiation-induced changes in characteristics might be transitory or long-lasting. In this work, an attempt was made to better understand the types of radiation-induced flaws and their significance in changing the characteristics of the materials.

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